

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = +25^\circ\text{C}$
-60V	250m Ω @ $V_{GS} = -10\text{V}$	-2.1A
	300m Ω @ $V_{GS} = -4.5\text{V}$	-1.9A

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features and Benefits

- Low gate drive
- Low input capacitance
- Fast switching speed
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

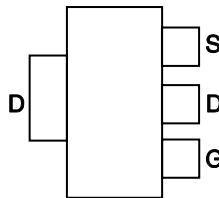
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish - Matte Tin annealed over Copper lead frame.
Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (approximate)

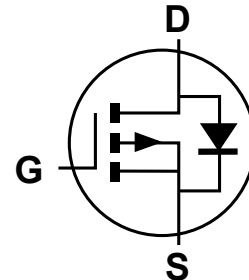
SOT223



Top View



Pin Out - Top View



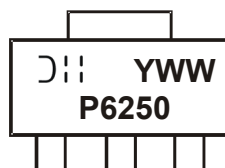
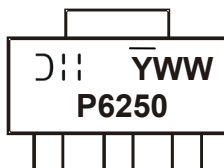
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
DMP6250SE-13	Standard	SOT223	2,500 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



⌐⌐⌐ = Manufacturer's Marking

P6250 = Marking Code

YWW = Date Code Marking for SAT (Shanghai Assembly/ Test site)

YWW = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Y or Y= Year (ex: 3 = 2013)

WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source voltage		V _{DSS}	-60	V
Gate-Source voltage (Note 5)		V _{GS}	±20	V
Continuous Drain current (Note 6) V _{GS} = -10V	T _A = +25°C	I _D	-2.1	A
	T _A = +70°C		-1.7	
	T _C = +25°C	I _D	-6.1	A
	T _C = +70°C		-4.9	
Maximum Body Diode Continuous Current		I _S	-1.8	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)		I _{DM}	-11	A
Single Pulsed Avalanche Current (Note 7) L = 0.1mH		I _{AS}	-12	A
Single Pulsed Avalanche Energy (Note 7) L = 0.1mH		E _{AS}	8	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.8	W
	T _A = +70°C		1.1	
Thermal Resistance, Junction to Ambient (Note 6)		R _{θJA}	69	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	P _D	14	W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	8.7	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	I _D = -250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	-1	—	-3	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	—	250	mΩ	V _{GS} = -10V, I _D = -1.0A
				300		V _{GS} = -4.5V, I _D = -0.5A
Diode Forward Voltage	V _{SD}	—	—	-1.2	V	V _{GS} = 0V, I _S = -2.0A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	551	—	pF	V _{DS} = -30V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	25.7	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	19.1	—	pF	
Gate Resistance	R _g	—	12.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	4.8	—	nC	V _{DS} = -30V, I _D = -2A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	9.7	—	nC	
Gate-Source Charge	Q _{gs}	—	1.5	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.6	—	nC	
Turn-On Delay Time	t _{D(on)}	—	6.3	—	ns	V _{DS} = -30V, V _{GS} = -10V, R _G = 50Ω, I _D = -1A
Turn-On Rise Time	t _r	—	10.3	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	91.4	—	ns	
Turn-Off Fall Time	t _f	—	39.8	—	ns	
Reverse recovery time	t _{rr}	—	9.2	—	ns	I _S = -1A, di/dt = 100A/μs
Reverse recovery charge	Q _{rr}	—	3.9	—	nC	

- Notes:
5. AEC-Q101 V_{GS} maximum is ±16V.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. IAR and EAR rating are based on low frequency and duty cycles to keep T_J = 25°C
 8. Short duration pulse test used to minimize self-heating effect.
 9. For design aid only, not subject to production testing.

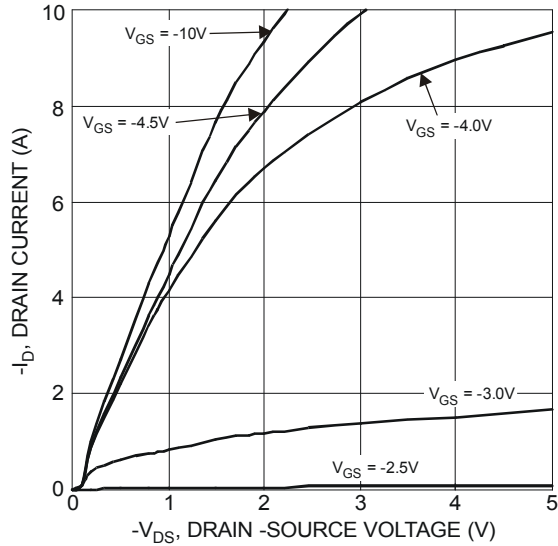


Figure 1 Typical Output Characteristics

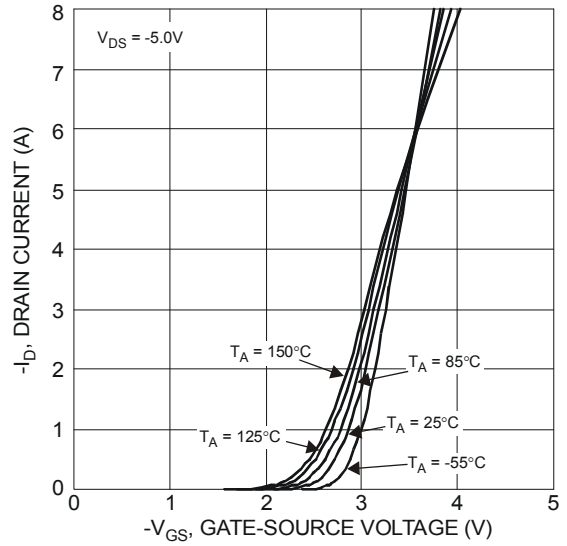


Figure 2 Typical Transfer Characteristics

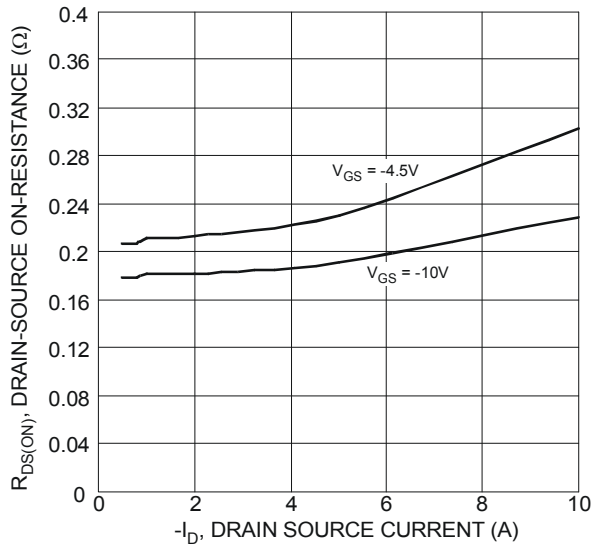


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

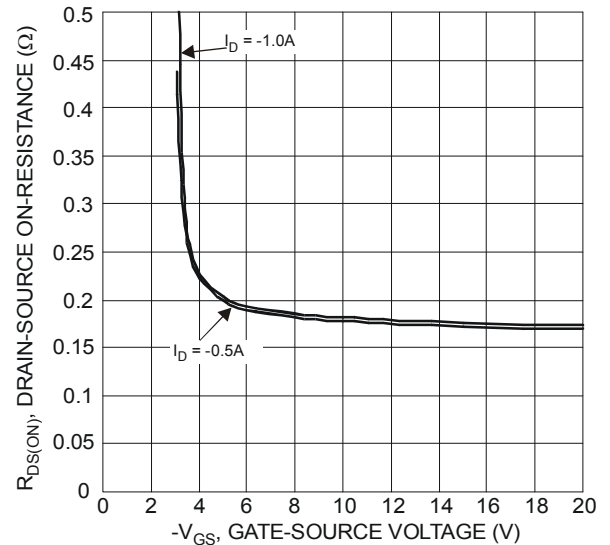


Figure 4 Typical Transfer Characteristics

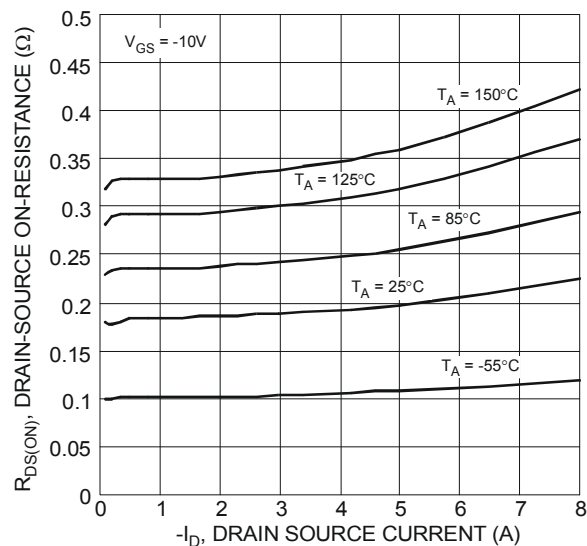


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

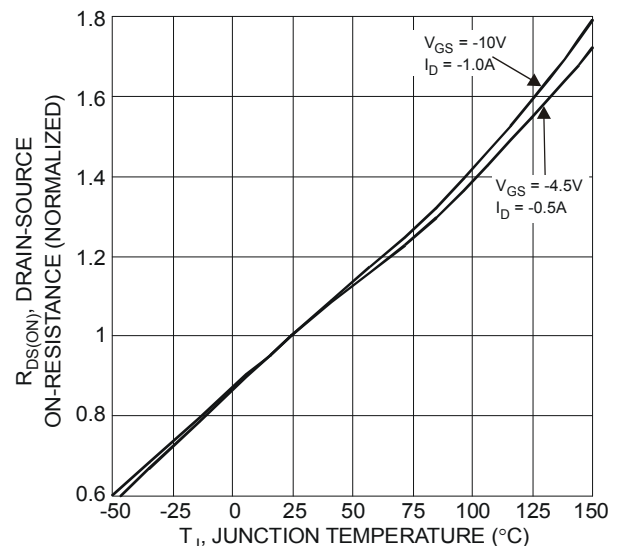


Figure 6 On-Resistance Variation with Temperature

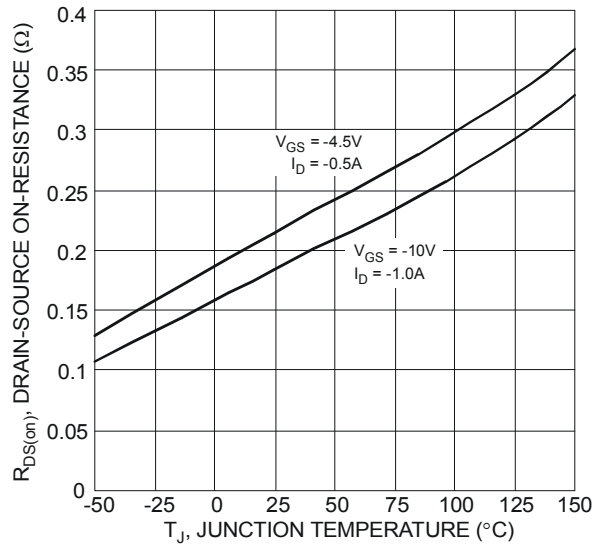


Figure 7 On-Resistance Variation with Temperature

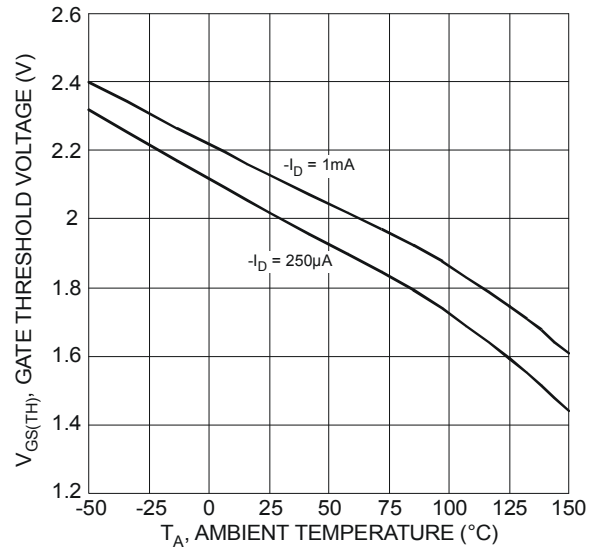


Figure 8 Gate Threshold Variation vs. Ambient Temperature

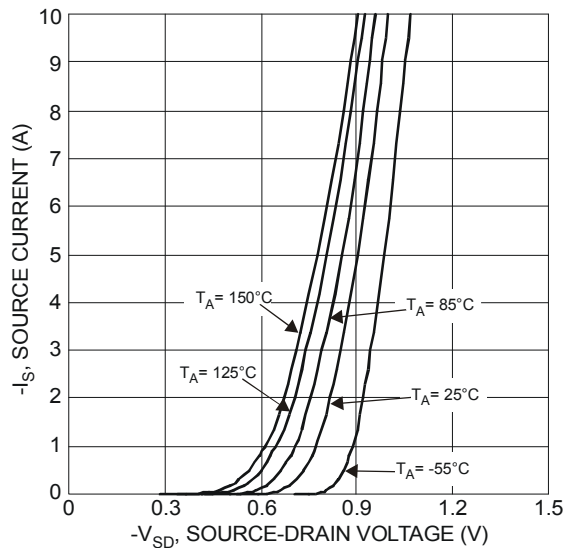


Figure 9 Diode Forward Voltage vs. Current

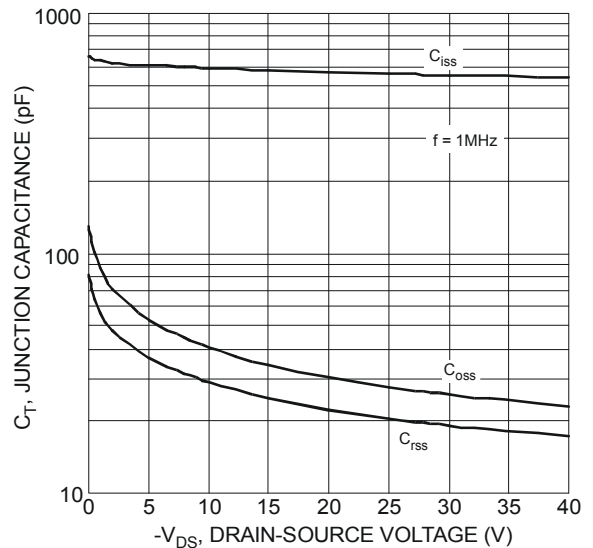


Figure 10 Typical Junction Capacitance

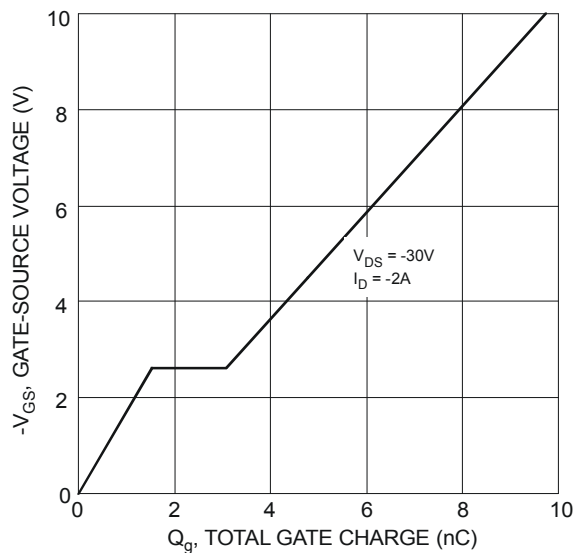


Figure 11 Gate-Charge Characteristics

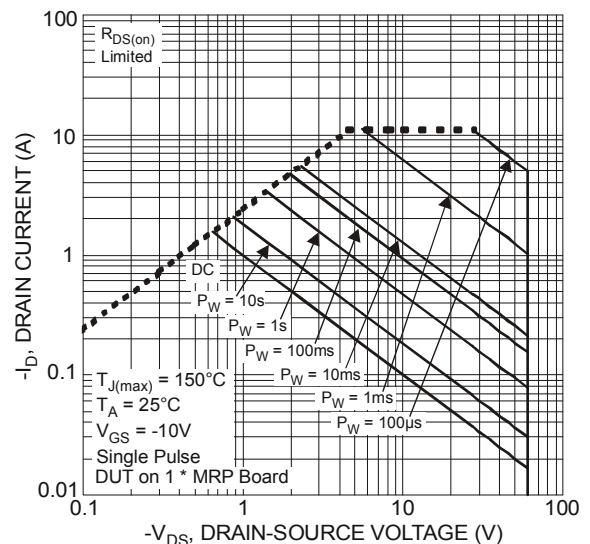
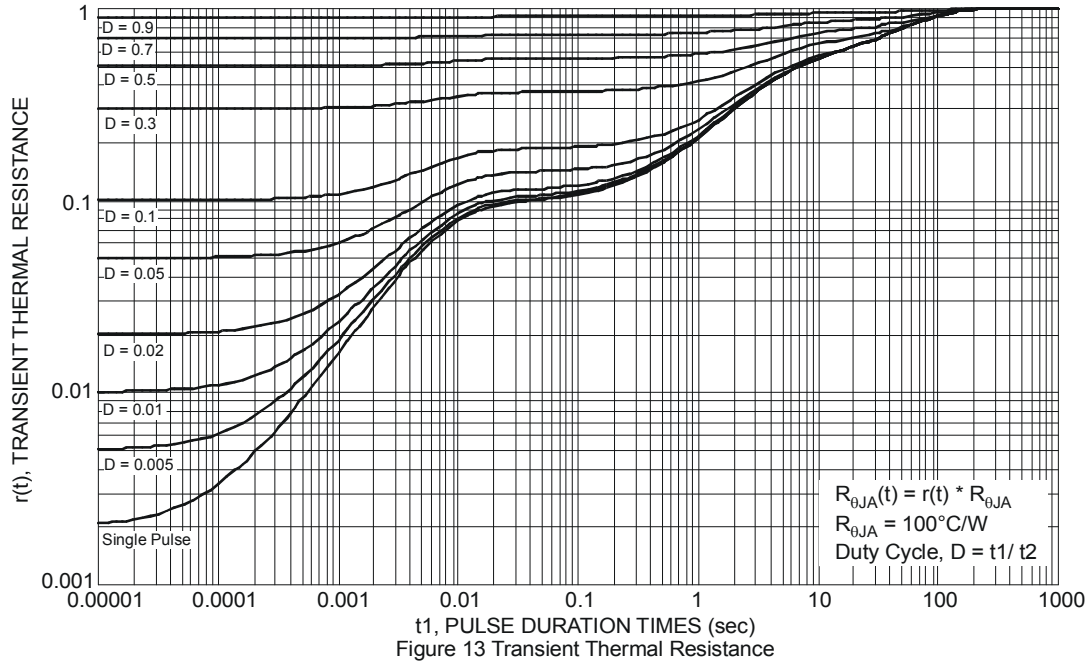
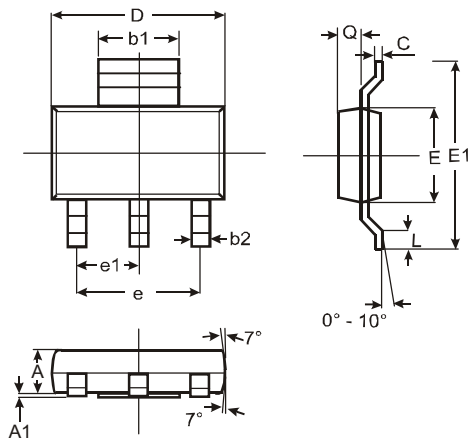


Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

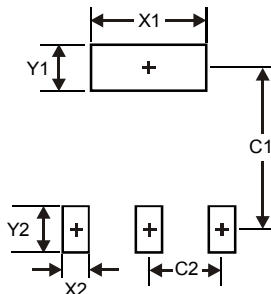
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b1	2.90	3.10	3.00
b2	0.60	0.80	0.70
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	—	—	4.60
e1	—	—	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3

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Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331